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(54) **INTEGRATED CIRCUIT FOR GATE
 OVERVOLTAGE PROTECTION OF POWER
 DEVICES**

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(57) **ABSTRACT**

An integrated gate overvoltage protection circuit for protecting the gate of a main field effect transistor (FET). The gate protection circuit includes a blocking FET and a discharge FET connected between the gate and the drain of the main FET. The gate overvoltage protection circuit is configured to turn on both the first FET and the second FET in the event of a fault condition, such that charge from the gate of the main FET is discharged through the first FET and the second FET to the drain of the main FET, thereby protecting the gate of the main FET.

